

### November 2013

# FDPF085N10A N-Channel PowerTrench<sup>®</sup> MOSFET 100 V, 40 A, 8.5 mΩ

### **Features**

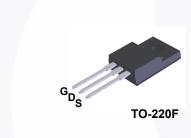
- $R_{DS(on)}$  = 6.5 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 40 A
- · Fast Switching Speed
- Low Gate Charge, Q<sub>G</sub> = 31 nC (Typ.)
- High Performance Trench Technology for Extremely Low  $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

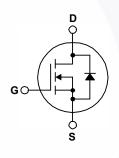
## Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- Consumer Appliances
- LED TV
- · Synchronous Rectification for ATX / Sever / Telecom PSU
- · Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FDPF085N10A	Unit
V <sub>DSS</sub>	Drain to Source Voltage		100	V	
V <sub>GSS</sub>	Gate to Source Voltage			±20	V
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		40	•
		- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		28	— A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	160	А
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			269	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns	
P <sub>D</sub>	Devuer Dissignation	$(T_{\rm C} = 25^{\rm o}{\rm C})$		33.3	W
	Power Dissipation	- Derate Above 25°C		0.22	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +175	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

### **Thermal Characteristics**

Symbol	Parameter	FDPF085N10A	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	4.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0/00

Part Number Top Mark Pag		Package	Packing Method	Reel Size	)	Tape Width	Qu	antity	
-		TO-220F	Tube			N/A	50 units		
Electrica	I Chara	acteristics T <sub>C</sub> = 25	5ºC unless ot	herwise noted.					
Symbol		Parameter		Test Condition	ons	Min.	Тур.	Max.	Unit
Off Charac	teristics	ذ							
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage		age I	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V				-	V
$\Delta BV_{DSS}$		wn Voltage Temperature				100			
$/\Delta T_J$	Coefficie	<b>U</b> 1	1	$I_D = 250 \ \mu A$ , Referenced to $25^{\circ}C$		-	0.07	-	V/ºC
	Zara Cal	ta Valtago Droin Curroni	١	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V		-	-	1	
IDSS	Zero Gai	ate Voltage Drain Current		$V_{DS} = 80 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$		-	-	500	μA
I <sub>GSS</sub>	Gate to F	Body Leakage Current	١	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	/	-	-	±100	nA
							-		1
On Charac									
V <sub>GS(th)</sub>		reshold Voltage		$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	•	2.0	-	4.0	V
R <sub>DS(on)</sub>		ain to Source On Resist		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 96 A		-	6.5	8.5	mΩ
9 <sub>FS</sub>	Forward	Transconductance		V <sub>DS</sub> = 10 V, I <sub>D</sub> = 96 A		-	76	-	S
Dynamic C	haracte	ristics							
C <sub>iss</sub>	Input Ca	pacitance		V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	2025	2695	pF
C <sub>oss</sub>	Output C	Capacitance				-	468	620	pF
C <sub>rss</sub>	Reverse	Transfer Capacitance				-	20	-	pF
C <sub>oss</sub> (er)	Engry Re	elated Output Capacitan	ce '	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V		-	752	-	pF
Q <sub>g(tot)</sub>	0,	te Charge at 10V		00 00		-	31	40	nC
Q <sub>gs</sub>		Source Gate Charge	,	$V_{GS} = 10 \text{ V}, V_{DS} = 50 \text{ V},$ $I_D = 96 \text{ A}$ (Note 4)		-	9.7	-	nC
Q <sub>gs2</sub>		arge Threshoid to Platea				-	5.0	-	nC
Q <sub>gd</sub>		Drain "Miller" Charge				-	7.5	-	nC
∽gu ESR		ent Series Resistance (G	-S) 1	f = 1 MHz		-	0.97	-	Ω
Switching	· ·	· · · · ·			I				
		Delay Time			T		18	46	ne
t <sub>d(on)</sub>		Rise Time	,	$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 96 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 4.7 \Omega$			22	40 54	ns
t <sub>r</sub> +							22		ns
t <sub>d(off)</sub>		Delay Time		63 7 6	_	-		68	ns
t <sub>f</sub>	Turn-Oii	Fall Time			(Note 4)	-	8	26	ns
Drain-Sou	rce Diod	e Characteristics							
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current				-	-	40	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode F		e Diode Forw	Forward Current		-	-	160	Α
V <sub>SD</sub>	Drain to S	Source Diode Forward V	/oltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 96 A		-	-	1.3	V
t <sub>rr</sub>	Reverse	Recovery Time		$V_{DD} = 50 \text{ V}, \text{V}_{GS} = 0 \text{ V},$	Isp = 96 A.	-	59	-	ns
Q <sub>rr</sub>		Recovery Charge		$dI_{F}/dt = 100 A/\mu s$		-	80	-	nC

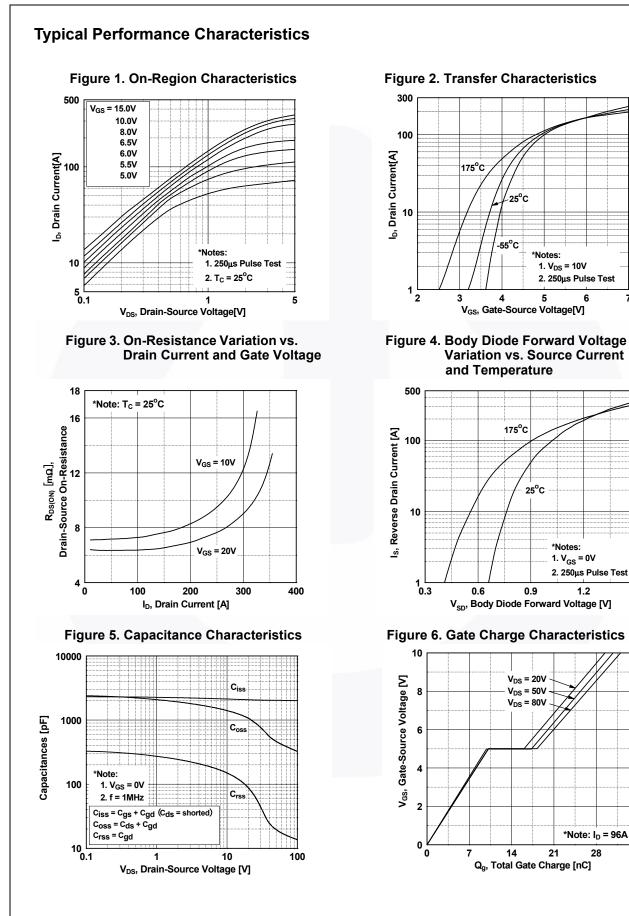
2. L = 3 mH, I<sub>AS</sub> = 13.4 A, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub> ≤ 40 A, di/dt ≤ 200 A/µs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature typical characteristics.

6

1.2

1.5

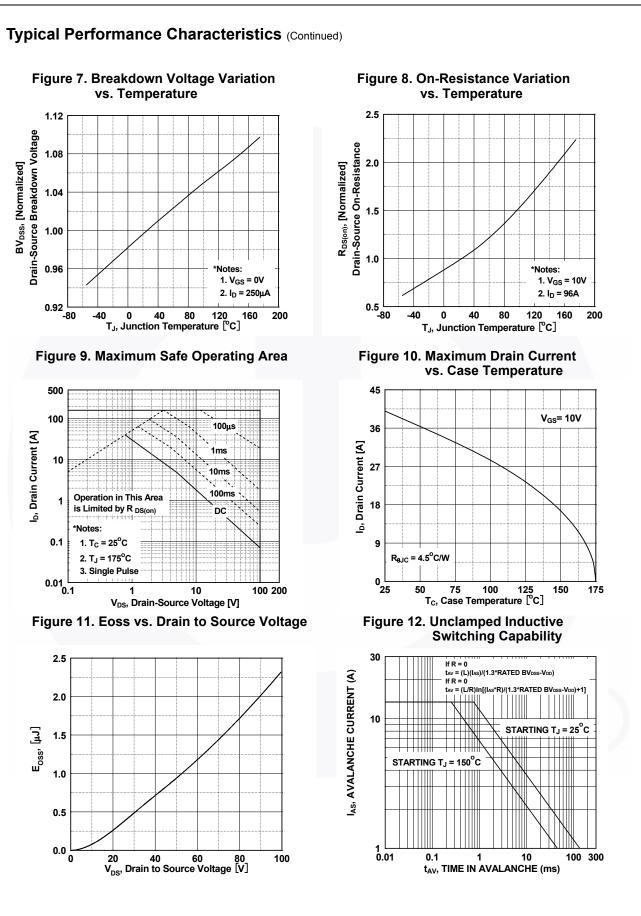
7



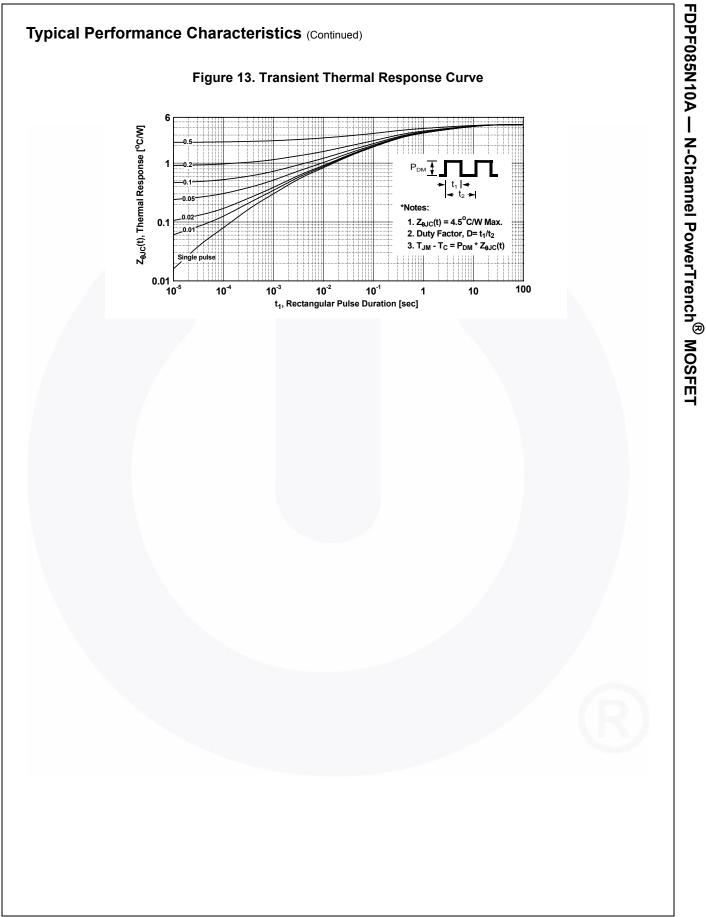
©2011 Fairchild Semiconductor Corporation FDPF085N10A Rev. C1

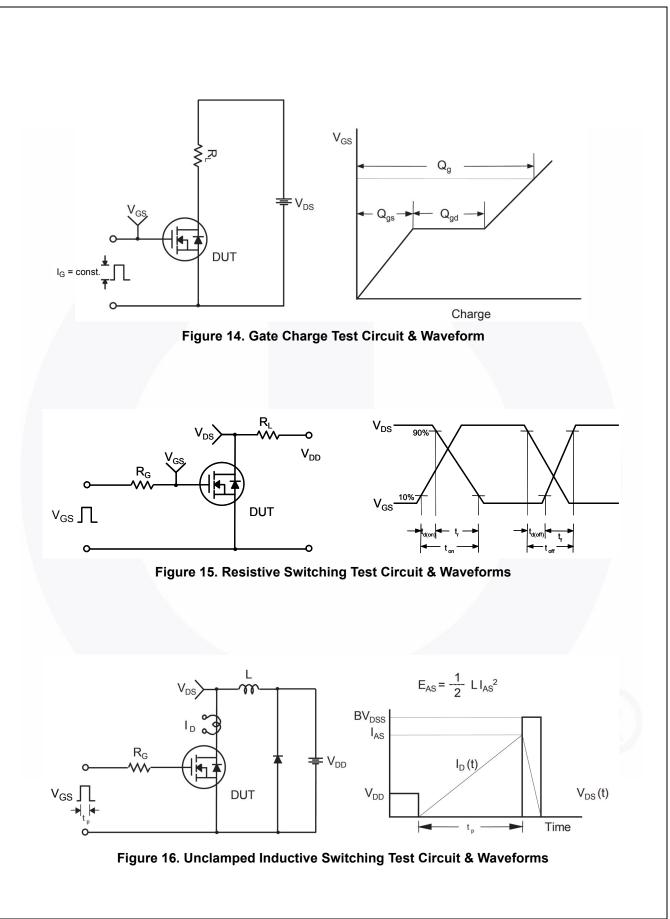
35

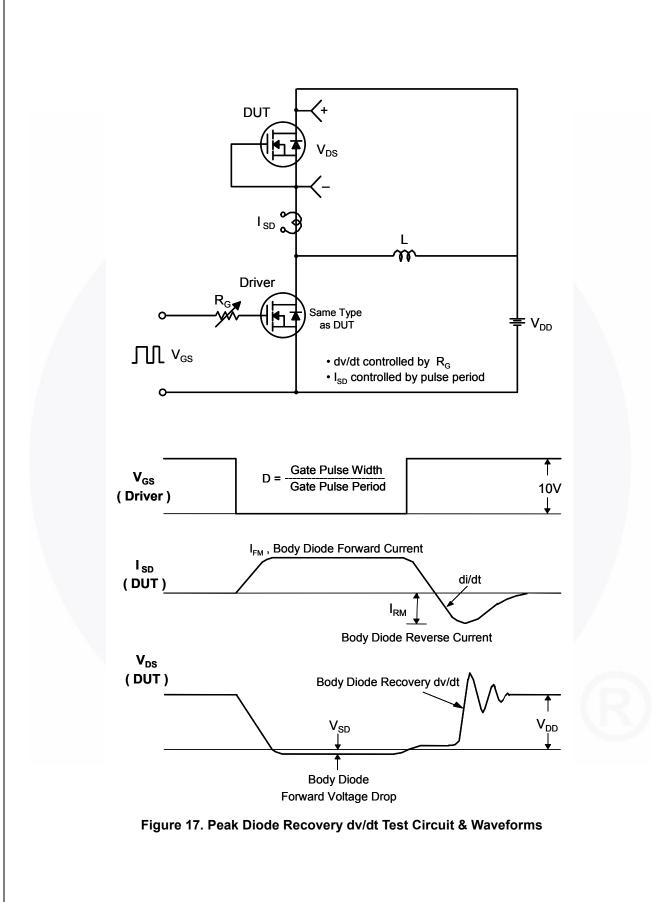
28

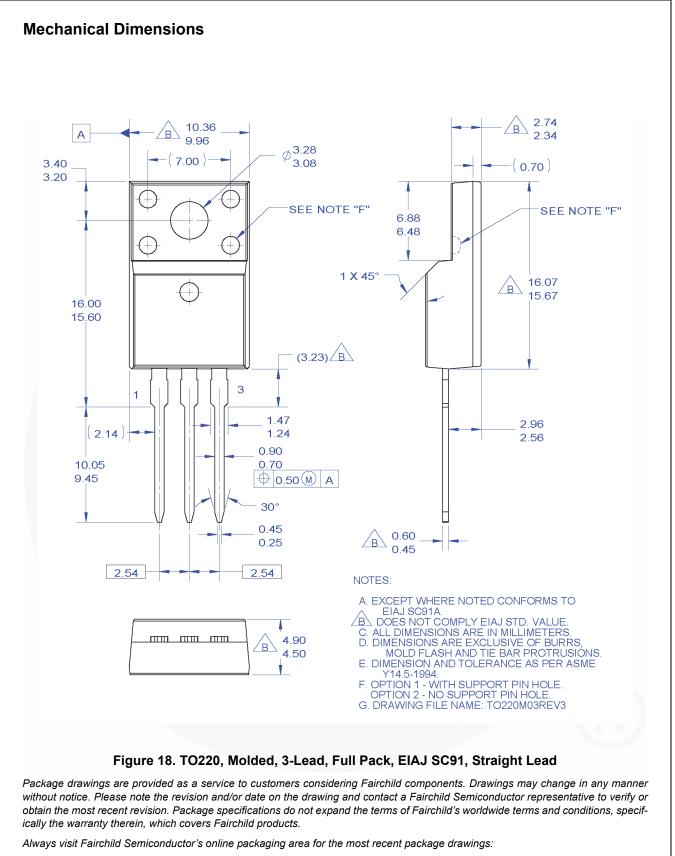


©2011 Fairchild Semiconductor Corporation FDPF085N10A Rev. C1









http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TF22S-003



SEMICONDUCTOR

#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™
AX-CAP <sup>®</sup> *	FRFET®
BitSiC™	Global Power Resource <sup>SM</sup>
Build it Now™	GreenBridge™
CorePLUS™	Green FPS™
CorePOWER™	Green FPS™ e-Series™
CROSSVOLT™	Gmax™
CTL™	GTO™
Current Transfer Logic™	IntelliMAX™
DEUXPEED®	ISOPLANAR™
Dual Cool™	Marking Small Speakers Sound Louder
EcoSPARK®	and Better™
EfficentMax™	MegaBuck™
ESBC™	MICROCOUPLER™
	MicroFET™
	MicroPak™
Fairchild <sup>®</sup>	MicroPak2™
Fairchild Semiconductor <sup>®</sup>	MillerDrive™
FACT Quiet Series™	MotionMax™
FACT Quiet Series ***	mWSaver®
FACT <sup>®</sup>	OptoHiT™
FASI-	OPTOL O OLO®

 $(b)_{\mathbb{R}}$ PowerTrench® PowerXS™ Programmable Active Droop™ QFET QS™ Quiet Series™ RapidConfigure™ Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™ Solutions for Your Success™ SPM<sup>®</sup> STEALTH™ SuperFET<sup>®</sup> SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SvncFET™

Sync-Lock™ SYSTEM<sup>®\*</sup> GENERAL TinyBoost<sup>®</sup> TinyBuck® TinyCalc™ TinyLogic® TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®\* uSerDes™ UHC® Ultra FRFET™ UniFFT™ VCX™ VisualMax™

VoltagePlus™

XS™

FDPF085N10A — N-Channel PowerTrench<sup>®</sup> MOSFE1

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**OPTOLOGIC®** 

**OPTOPLANAR<sup>®</sup>** 

#### DISCLAIMER

FastvCore™

**FETBench™** 

FPS™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### **PRODUCT STATUS DEFINITIONS** Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC